

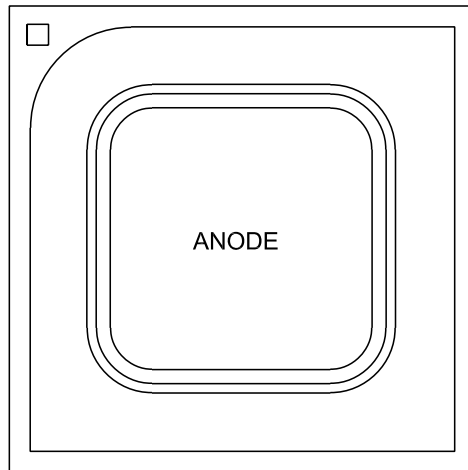
PROCESS CPD98V
Schottky Diode
Silicon High Current Schottky Diode Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Anode Bonding pad Area	6.3 x 6.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

93,826

PRINCIPAL DEVICE TYPES

CMUSH2-4 Series

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
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R0 (20- January 2006)